STK551U3A2A-E

Thick-Film Hybrid IC

Inverter Power H-IC for 3-phase Motor Drive



Overview

This "Inverter Power H-IC" is highly integrated device containing all High Voltage (HV) control from HV-DC to 3-phase outputs in a single SIP module (Single-In line Package). Output stage uses IGBT/FRD technology and implements Under Voltage Protection (UVP) and Over Current Protection (OCP) with a Fault Detection output flag. Internal Boost diodes are provided for high side gate boost drive.

Function

- Single control power supply due to Internal bootstrap circuit for high side pre-driver circuit
- All control input and status output are at low voltage levels directly compatible with microcontrollers
- Built-in dead time for shoot-thru protection
- Externally accessible embedded thermistor for substrate temperature measurement
- The level of the over-current protection current is adjustable with the external resistor, "RSD"

Certification

• UL1557 (File Number : E339285).

Specifications

Absolute Maximum Ratings at Tc = 25°C

Parameter	Symbol	Conditions		Ratings	Unit
Supply voltage	VCC	V+ to V-, surge < 500V	*1	450	V
Collector-emitter voltage	VCE	V+ to U,V,W or U,V,W to V-		600	V
		V+, V-, U,V,W terminal current		±20	А
Output current	lo	V+, V-, U,V,W terminal current at Tc = 100°C		±10	А
Output peak current	Іор	V+, V-, U,V,W terminal current for a Pulse width of 1ms.		±40	А
Pre-driver voltage	VD1,2,3,4	VB1 to U, VB2 to V, VB3 to W, VDD to VSS *2		20	V
Input signal voltage	VIN	HIN1, 2, 3, LIN1, 2, 3		–0.3 to VDD	V
FAULT terminal voltage	VFAULT	FAULT terminal		-0.3 to VDD	V
Maximum power dissipation	Pd	IGBT per channel		39	W
Junction temperature	Tj	IGBT,FRD		150	°C
Storage temperature	Tstg			-40 to +125	°C
Operating case temperature	Тс	H-IC case temperature		-40 to +100	°C
Tightening torque		Case mounting screws	*3	1.0	Nm
Withstand voltage	Vis	50Hz sine wave AC 1 minute	*4	2000	VRMS

Reference voltage is "VSS" terminal voltage unless otherwise specified.

- *1: Surge voltage developed by the switching operation due to the wiring inductance between + and U-(V-, W-) terminal.
- *2: Terminal voltage: VD1=VB1-U, VD2=VB2-V, VD3=VB3-W, VD4=VDD-VSS
- *3: Flatness of the heat-sink should be 0.15mm and below.
- *4: Test conditions : AC2500V, 1 second.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ORDERING INFORMATION

See detailed ordering and shipping information on page 15 of this data sheet.

STK551U3A2A-E

Electrical Characteristics at Tc = 25°C, VD1, VD2, VD3, VD4 = 15V

Parameter	Symbol Conditions		Test		Ratings	-	Unit	
Faranielei	Symbol	0	nutions	circuit	min	typ	max	Unit
Power output section								
Collector-emitter cut-off current	ICE	VCE = 600V		Fig. 4	-	-	0.1	mA
Bootstrap diode reverse current	IR(BD)	VR(BD)		Fig.1	-	-	0.1	mA
		lo = 20A	Upper side		-	1.9	2.7	
Collector to emitter		Tj = 25°C	Lower side *1	5.0	-	2.3	3.1	
saturation voltage	VCE(SAT)	lo = 10A	Upper side	Fig.2	-	1.6	-	V
		Tj = 100°C	Lower side *1		-	1.8	-	
		lo = 20A	Upper side		-	2.1	2.8	
		Tj = 25°C	Lower side *1		-	2.5	3.2	
Diode forward voltage	VF	lo = 10A	Upper side	Fig.3	-	1.6	-	V
		Tj = 100°C	Lower side *1		-	1.8	-	
Junction to case	θj-c(T)	IGBT			-	-	3.2	
thermal resistance	θj-c(D)	FRD			-	-	5	°C/W
Control (Pre-driver) section	•					•	•	
			VD1, 2, 3 = 15V		-	0.08	0.4	
Pre-driver power dissipation	ID	VD4 = 15V		Fig.4	-	1.6	4	mA
High level Input voltage	Vin H				2.5	-	-	V
Low level Input voltage	Vin L	HIN1, HIN2, H	,		-	-	0.8	V
Input threshold voltage hysteresis*1	Vinth(hys)	LIN1, LIN2, LI	N3 to VSS		0.5	0.8	-	V
Logic 1 input leakage current	l _{IN+}	VIN = +3.3V			-	100	143	μA
Logic 0 input leakage current	I _{IN-}	VIN = 0V			-	-	2	μA
FAULT terminal input electric current	loSD	FAULT : ON/\	FAULT = 0.1V		-	2	-	mA
FAULT clear time	FLTCLR	Fault output la	tch time.		18	-	80	ms
V_{CC} and V_{S} undervoltage positive going threshold.	V _{CCUV+} V _{SUV+}				10.5	11.1	11.7	v
V_{cc} and V_s undervoltage negative going threshold.	V _{CCUV} - V _{SUV} -				10.3	10.9	11.5	v
V_{CC} and V_S undervoltage hysteresis	VCCUVH VSUVH-				0.14	0.2	-	А
Over current protection level	ISD	PW = 100µs,	RSD = 0Ω	Fig.5	32.7	-	41.5	А
Output level for current monitor	ISO	lo = 20A			0.37	0.40	0.43	V
Thermistor for substrate temperature	Rt	Thermistor Re at 25°C (Vth)	sistance		90	100	110	kΩ

Reference voltage is "VSS" terminal voltage unless otherwise specified.

*1: The lower side's VCE(SAT) and VF include a loss by the shunt resistance

Description			Test	Ratings			
Parameter	Symbol Conditions		circuit	min	typ	max	Unit
Switching Character							
	tON	lo = 20A		0.3	0.4	1.1	
Switching time	tOFF	Inductive load		-	0.7	1.4	μs
Turn-on switching loss	Eon	$Ic = 10A, V^{+} = 300V,$		-	295	-	μJ
Turn-off switching loss	Eoff	V _{DD} = 15V, L = 3.9mH	F i 0	-	230	-	μJ
Total switching loss	Etot	Tc = 25°C	Fig.6	-	525	-	μJ
Turn-on switching loss	Eon	Ic = 10A, V ⁺ = 300 V,		-	365	-	μJ
Turn-off switching loss	Eoff	V _{DD} = 15V, L = 3.9mH		-	290	-	μJ
Total switching loss	Etot	Tc = 100°C		-	655	-	μJ
Diode reverse recovery energy	Erec	I _F = 10A, V ⁺ = 400V, V _{DD} = 15V,		-	13	-	μJ
Diode reverse recovery time	Trr	L = 3.9mH, Tc = 100°C		-	57	-	ns
Reverse bias safe operating area	RBSOA	Io = 40A, VCE = 450V			Full square		
Short circuit safe operating area	SCSOA	VCE = 400V, Tc = 100°C		4	-	-	μs
Allowable offset voltage slew rate	dv/dt	Between U,V,W to U-,V-,W-		-50	-	50	V/ns

Reference voltage is "VSS" terminal voltage unless otherwise specified.

Notes:

1. When the internal protection circuit operates, a Fault signal is turned ON (When the Fault terminal is low level, Fault signal is ON state : output form is open DRAIN) but the Fault signal does not latch. After protection operation ends, it returns automatically within about 18ms to 80ms and resumes operation beginning condition. So, after Fault signal detection, set all input signals to OFF (Low) at once. However, the operation of pre-drive power supply low voltage protection (UVLO: with hysteresis about 0.2V) is as follows.

Upper side:

The gate is turned off and will return to regular operation when recovering to the normal voltage, but the latch will continue till the input signal will turn 'low'.

Lower side:

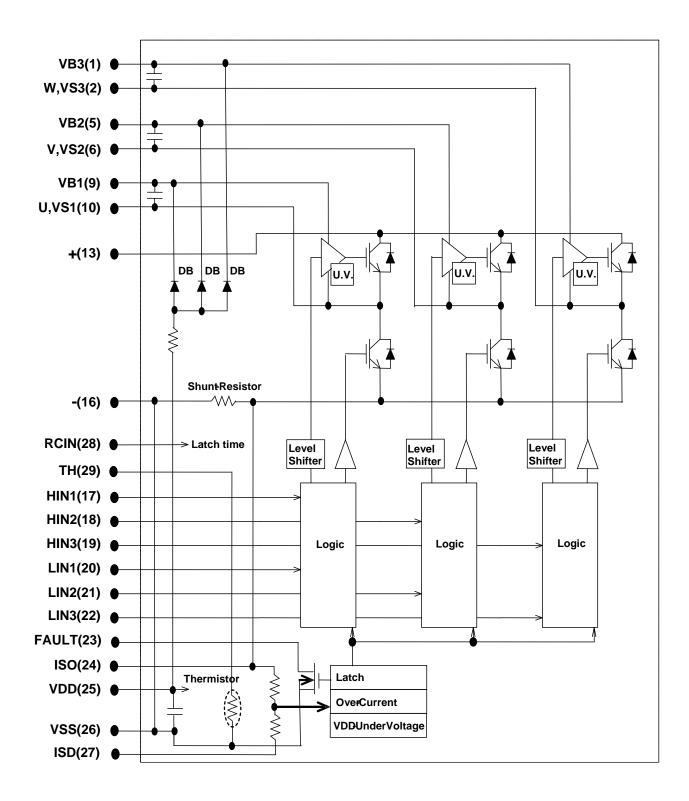
The gate is turned off and will automatically reset when recovering to normal voltage. It does not depend on input signal voltage.

- 2. When assembling the H-IC on the heat sink with M3 type screw, tightening torque range is 0.6 Nm to 0.9 Nm.
- 3. The pre-drive low voltage protection is the feature to protect devices when the pre-driver supply voltage falls due to an operating malfunction.

Module Pin-Out Description

Pin No.	Name	Description		
1	VB3	High Side Floating Supply Voltage 3		
2	W, VS3	Output 3 - High Side Floating Supply Offset Voltage		
3	—	Without Pin		
4	_	Without Pin		
5	VB2	High Side Floating Supply voltage 2		
6	V,VS2	Output 2 - High Side Floating Supply Offset Voltage		
7	—	Without Pin		
8	—	Without Pin		
9	VB1	High Side Floating Supply voltage 1		
10	U,VS1	Output 1 - High Side Floating Supply Offset Voltage		
11	—	Without Pin		
12	_	none		
13	V+	Positive Bus Input Voltage		
14	NA	none		
15	NA	none		
16	V-	Negative Bus Input Voltage		
17	HIN1	Logic Input High Side Gate Driver - Phase 1		
18	HIN2	Logic Input High Side Gate Driver - Phase V		
19	HIN3	Logic Input High Side Gate Driver - Phase W		
20	LIN1	Logic Input Low Side Gate Driver - Phase U		
21	LIN2	Logic Input Low Side Gate Driver - Phase V		
22	LIN3	Logic Input Low Side Gate Driver - Phase W		
23	FLTEN	Enable input / Fault output		
24	ISO	Current monitor output		
25	VDD	+15V Main Supply		
26	VSS	Negative Main Supply		
27	ISD	Over current detection and setting		
28	RCIN	Fault clear time setting output		
29	ТН	Thermistor output		

Equivalent Block Diagram



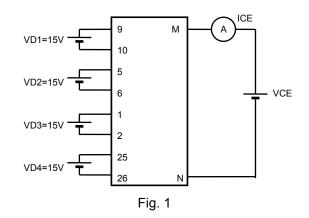
Test Circuit

(The tested phase : U+ shows the upper side of the U phase and U- shows the lower side of the U phase.)

■ ICE / IR(BD)

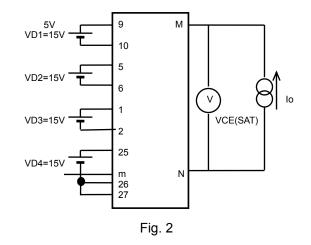
	U+	V+	W+	U-	V-	W-
М	13	13	13	10	6	2
Ν	10	6	2	16	16	16

	U(BD)	V(BD)	W(BD)
М	9	5	1
N	26	26	26



■ VCE(SAT) (Test by pulse)

	U+	V+	W+	U-	V-	W-
М	13	13	13	10	6	2
Ν	10	6	2	16	16	16
m	17	18	19	20	21	22



■ VF (Test by pulse)

	U+	V+	W+	U-	V-	W-
М	13	13	13	10	6	2
Ν	10	6	2	16	16	16

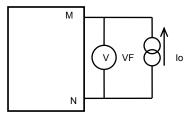


Fig. 3

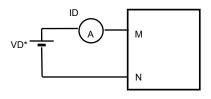
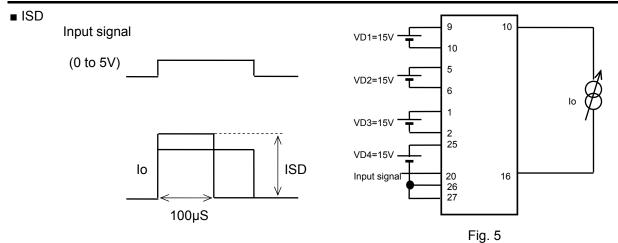


Fig. 4

∎ ID

	VD1	VD2	VD3	VD4
М	9	5	1	25
N	10	6	2	26

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Switching time (The circuit is a representative example of the lower side U phase.)

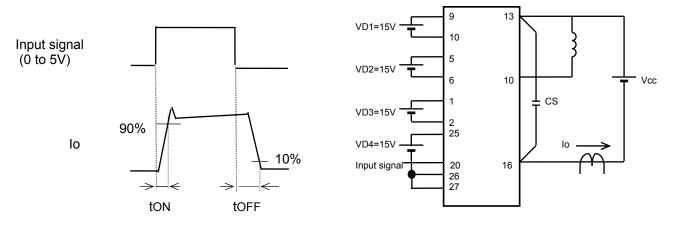
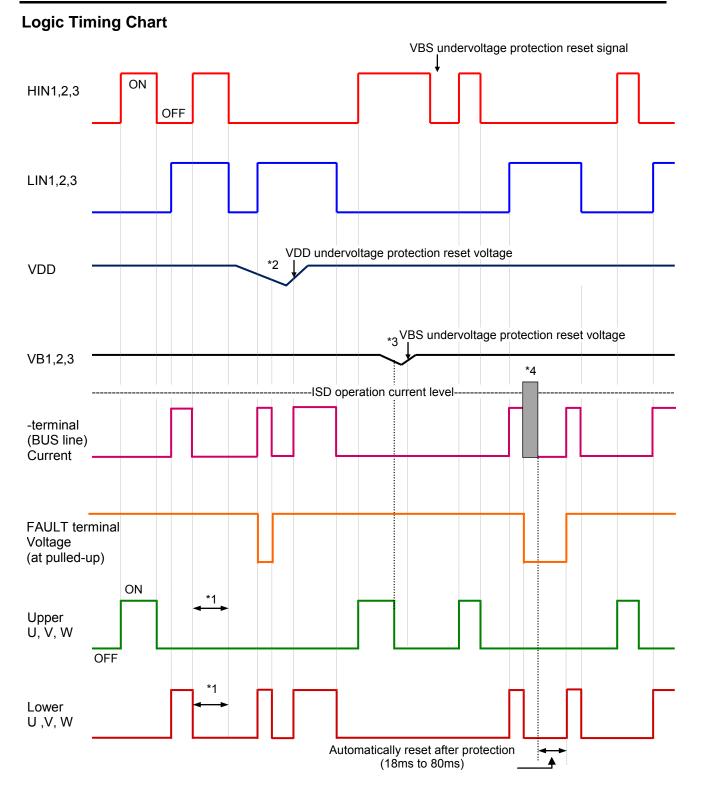


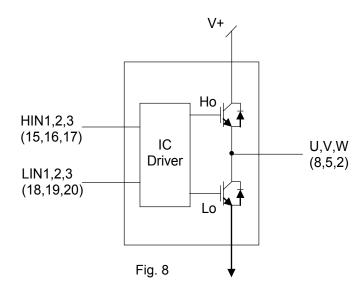
Fig. 6



<u>Notes</u>

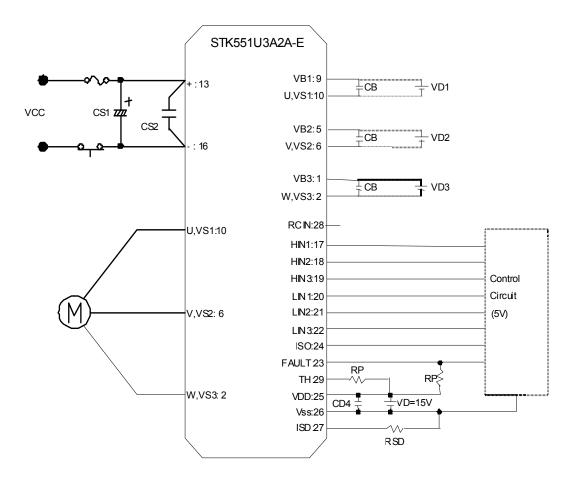
- Fig. 7
- *1: Diagram shows the prevention of shoot-through via control logic. More dead time to account for switching delay needs to be added externally.
- *2 : When VDD decreases all gate output signals will go low and cut off all of 6 IGBT outputs. part. When VDD rises the operation will resume immediately.
- *3: When the upper side gate voltage at VB1, VB2 and VB3 drops only, the corresponding upper side output is turned off. The outputs return to normal operation immediately after the upper side gat voltage rises.
- *4 : In case of over current detection, all IGBT's are turned off and the FAULT output is asserted. Normal operation resumes in 18 to 80ms after the over current condition is removed.

Logic level table



FLTEN	Itrip	HIN1,2,3	LIN1,2,3	U,V,W
1	0	1	0	Vbus
1	0	0	1	0
1	0	0	0	Off
1	0	1	1	Off
1	1	х	Х	Off
0	х	х	Х	Off

Sample Application Circuit





Recommended Ope	Recommended Operating Conditions at Tc = 25°C										
Item	Sumbol	Conditions			Ratings						
item	Symbol Conditions			min	typ						
Supply voltage	VCC	+ to U-(V-,W-)		0	280						
Pre-driver	VD1,2,3	VB1 to U, VB2 to V, VB3 to W		12.5	15						
supply voltage	VD4	VDD to VSS	*1	13.5	15						

р 30 450 V 5 17.5 v 5 16.5 ON-state input voltage VIN(ON) 3.0 50 HIN1, HIN2, HIN3, V VIN(OFF) LIN1, LIN2, LIN3 OFF-state input voltage 0 _ 0.3 PWM frequency fPWM 1 20 kHz DT Turn-off to turn-on 2 μs Dead time --Allowable input pulse width PWIN ON and OFF 1 _ μS 0.6 0.9 Tightening torque 'M3' type screw Nm

*1 Pre-drive power supply (VD4=15±1.5V) must be have the capacity of Io=20mA(DC), 0.5A(Peak).

Usage Precautions

- 1. This H-IC includes bootstrap diode and resistors. Therefore, by adding a capacitor "CB", a high side drive voltage is generated; each phase requires an individual bootstrap capacitor. The recommended value of CB is in the range of 1 to 47μ F, however this value needs to be verified prior to production. If selecting the capacitance more than $47\mu F$ (±20%), connect a resistor (about 20Ω) in series between each 3-phase upper side power supply terminals (VB1,2,3) and each bootstrap capacitor. When not using the bootstrap circuit, each upper side pre-drive power supply requires an external independent power supply.
- It is essential that wirning length between terminals in the snubber circuit be kept as short as possible to reduce the effect of 2. surge voltages. Recommended value of "CS" is in the range of 0.1 to 10μ F.
- "ISO" (pin24) is terminal for current monitor. When the pull-down resistor is used, please select it more than $5.6k\Omega$ 3.
- 4. "FAULT" (pin23) is open DRAIN output terminal. (Active Low). Pull up resistor is recommended more than 5.6kΩ.
- Inside the H-IC, a thermistor used as the temperature monitor for internal subatrate is connected between VSS terminal and 5. TH terminal, therefore, an external pull up resistor connected between the TH terminal and an external power supply should be used. The temperature monitor example application is as follows, please refer the Fig.10, and Fig.11 below.
- pull down resistor of $33k\Omega$ is provided internally at the signal input terminals. An external resistor of 2.2k to $3.3k\Omega$ should be 6. added to reduce the influence of external wiring noise.
- The over-current protection feature is not intended to protect in exceptional fault condition. An external fuse is recommended 7. for safety.
- When "-" and "VSS" terminal are short-circuited on the outside, level that over-current protection (ISD) might be changed 8. from designed value as H-IC. Please check it in your set ("N" terminal and "VSS" terminal are connected in H-IC).
- The over-current protection function operates normally when an external resistor RSD is connected between ISD and VSS 9. terminals. Be sure to connect this resistor. The level of the overcurrent protection can be changed according to the RSD value.
- When input pulse width is less than 1.0µs, an output may not react to the pulse. (Both ON signal and OFF signal) 10.

This data shows the example of the application circuit, does not guarantee a design as the mass production set.

Unit

max

The characteristic of thermistor

Parameter	Symbol	Condition	Min	Тур.	Max	Unit
Resistance	R ₂₅	Tc = 25°C	97	100	103	kΩ
Resistance	R ₁₀₀	Tc = 100°C	4.93	5.38	5.88	kΩ
B-Constant (25 to 50 °C)	В		4165	4250	4335	k
Temperature Range			-40	-	+125	°C

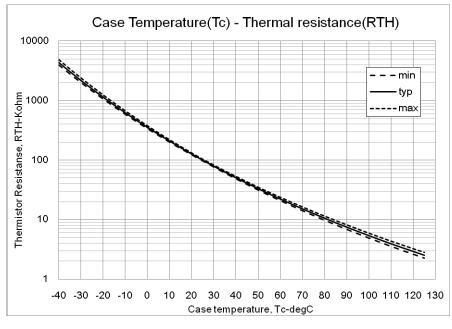
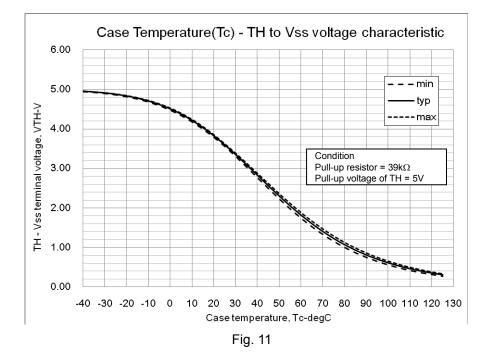


Fig. 10





The characteristic of PWM switching frequency

Maximum sinusoidal phase current as function of switching frequency (VBUS=400V, Tc=100°C)

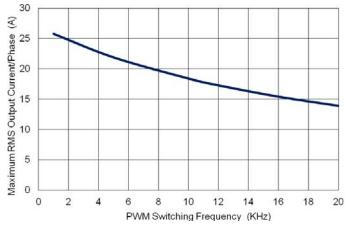
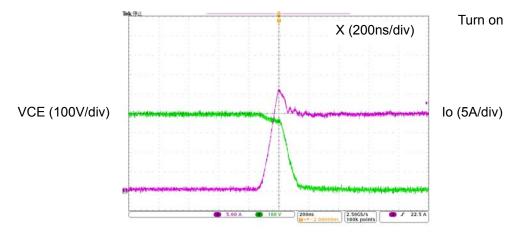


Fig.12

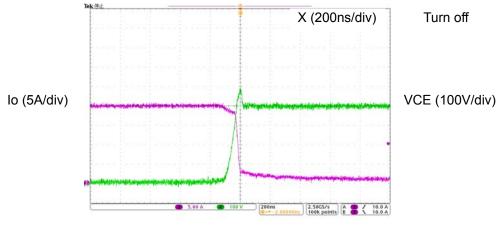
Switching waveform

IGBT Turn-on. Typical turn-on waveform @Tc=100deg, V_{BUS}=400V





IGBT Turn-off. Typical turn-off waveform @Tc=100deg, V_{BUS}=400V





CB capacitor value calculation for bootstrap circuit

Calculate condition

Item	Symbol	Value	Unit
Upper side power supply.	VBS	15	V
Total gate charge of output power IGBT at 15V.	Qg	153	nC
Upper side power supply low voltage protection.	UVLO	12	V
Upper side power dissipation.	IDmax	400	μA
ON time required for CB voltage to fall from 15V to UVLO	Ton-max	-	S

Capacitance calculation formula

CB must not be discharged below to the upper limit of the UVLO - the maximum allowable on-time (Ton-max) of the upper side is calculated as follows:

VBS * CB – Qg – IDmax * Ton-max = UVLO * CB CB = (Qg + IDmax * Ton-max) / (VBS – UVLO)

The relationship between Ton-max and CB becomes as follows. CB is recommended to be approximately 3 times the value calculated above. The recommended value of CB is in the range of 1 to 47μ F, however, the value needs to be verified prior to production.

Tonmax-Cb characteristic

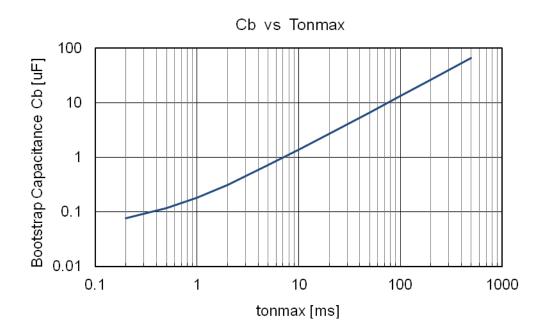


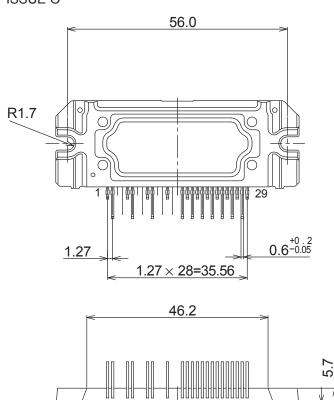
Fig 15

2.0

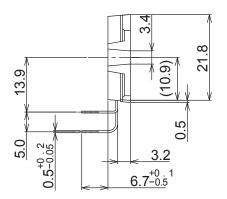
Package Dimensions

(unit : mm)

SIP29 56x21.8 CASE 127BW ISSUE O



50.0 62.0 missing pin : 3,4,7,8,11,12,14,15



ORDERING INFORMATION

Device	Package	Shipping (Qty / Packing)
STK551U3A2A-E	SIP29 56x21.8 (Pb-Free)	8 / Tube

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